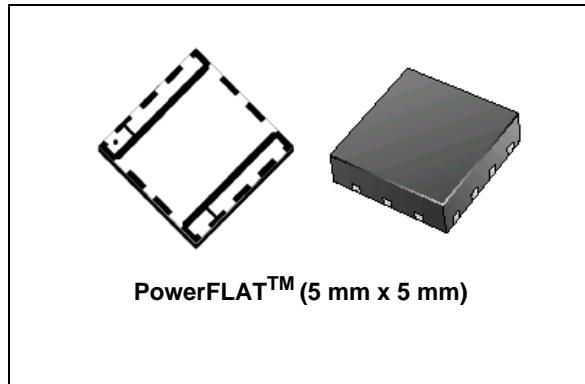


RF power transistor, LdmoST plastic family  
N-channel enhancement-mode lateral MOSFETs

## Features

- Excellent thermal stability
- Common source configuration
- $P_{OUT} = 8 \text{ W}$  with 13 dB gain @ 870 MHz / 7.5 V
- Plastic package
- ESD protection
- In compliance with the 2002/95/EC european directive



## Description

The PD84008L-E is a common source N-channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broadband commercial and industrial applications. It operates at 7.5 V in common source mode at frequencies of up to 1 GHz. PD84008L-E boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in leadless SMD plastic RF power package, PowerFLAT™.

Figure 1. Pin connection

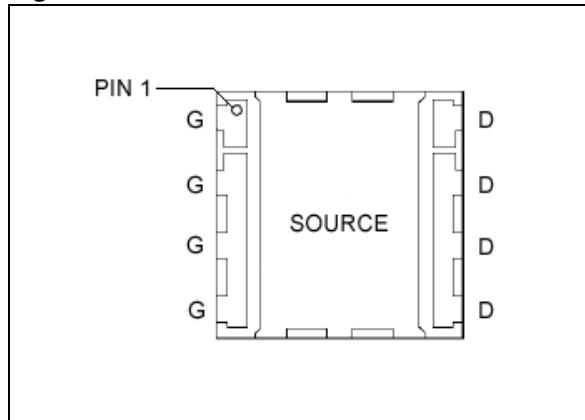


Table 1. Device summary

Order code	Marking	Package	Packing
PD84008L-E	84008	PowerFLAT™	Tape and reel

## Contents

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## 1 Electrical data

### 1.1 Maximum ratings

**Table 2. Absolute maximum ratings ( $T_{CASE} = 25^\circ\text{C}$ )**

Symbol	Parameter	Value	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source voltage	25	V
$V_{GS}$	Gate-source voltage	-0.5 to +15	V
$I_D$	Drain current	7	A
$P_{DISS}$	Power dissipation (@ $T_C = 70^\circ\text{C}$ )	26.7	W
$T_J$	Max. operating junction temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage temperature	-65 to +150	$^\circ\text{C}$

### 1.2 Thermal data

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{\text{thJC}}$	Junction - case thermal resistance	3	$^\circ\text{C}/\text{W}$

## 2 Electrical characteristics

$T_{CASE} = +25^\circ\text{C}$

### 2.1 Static

**Table 4. Static**

Symbol	Test conditions		Min	Typ	Max	Unit
$I_{DSS}$	$V_{GS} = 0 \text{ V}$	$V_{DS} = 25 \text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	$V_{GS} = 5 \text{ V}$	$V_{DS} = 0 \text{ V}$			1	$\mu\text{A}$
$V_{GS(Q)}$	$V_{DS} = 10 \text{ V}$	$I_D = 250\text{mA}$	3.2		4.8	V
$V_{DS(ON)}$	$V_{GS} = 10 \text{ V}$	$I_D = 1 \text{ A}$		0.27	0.31	V
$C_{ISS}$	$V_{GS} = 0 \text{ V}$	$V_{DS} = 7 \text{ V}$	$f = 1 \text{ MHz}$	57		pF
$C_{OSS}$	$V_{GS} = 0 \text{ V}$	$V_{DS} = 7 \text{ V}$	$f = 1 \text{ MHz}$	46		pF
$C_{RSS}$	$V_{GS} = 0 \text{ V}$	$V_{DS} = 7 \text{ V}$	$f = 1 \text{ MHz}$	2		pF

### 2.2 Dynamic

**Table 5. Dynamic**

Symbol	Test conditions	Min	Typ	Max	Unit
$P_{3dB}$	$V_{DD} = 7.5 \text{ V}$ , $I_{DQ} = 250 \text{ mA}$ , $f = 870 \text{ MHz}$	8	9		W
$G_P$	$V_{DD} = 7.5 \text{ V}$ , $I_{DQ} = 250 \text{ mA}$ , $P_{OUT} = 2 \text{ W}$ , $f = 870 \text{ MHz}$	13	15.5		dB
$h_D$	$V_{DD} = 7.5 \text{ V}$ , $I_{DQ} = 250 \text{ mA}$ , $P_{OUT} = P_{3dB}$ , $f = 870 \text{ MHz}$	50	57		%
Load mismatch	$V_{DD} = 9.5 \text{ V}$ , $I_{DQ} = 250 \text{ mA}$ , $P_{OUT} = 10 \text{ W}$ , $f = 870 \text{ MHz}$ All phase angles	20:1			VSWR

### 2.3 ESD protection characteristics

**Table 6. ESD protection characteristics**

Test conditions	Class
Human body model	2
Machine model	M3

### 2.4 Moisture sensitivity level

**Table 7. Moisture sensitivity level**

Test methodology	Rating
J-STD-020B	MSL 3

### 3 Impedance

Figure 2. Current conventions

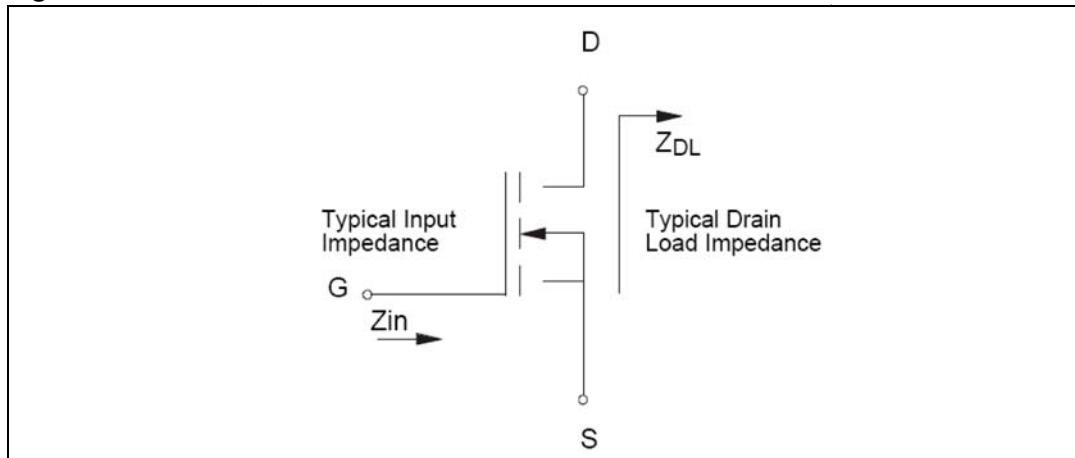
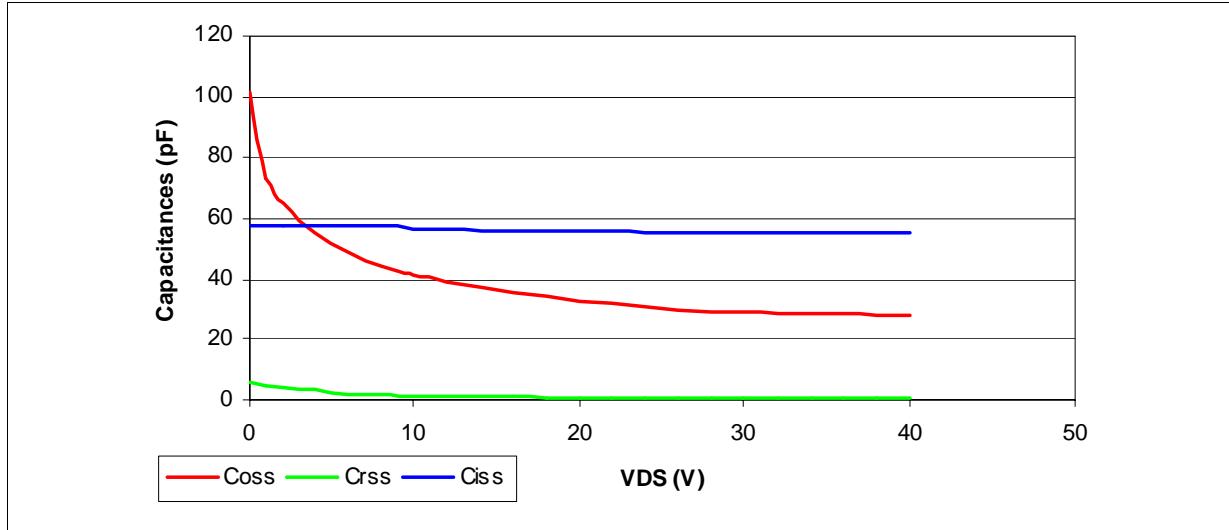


Table 8. Impedance data

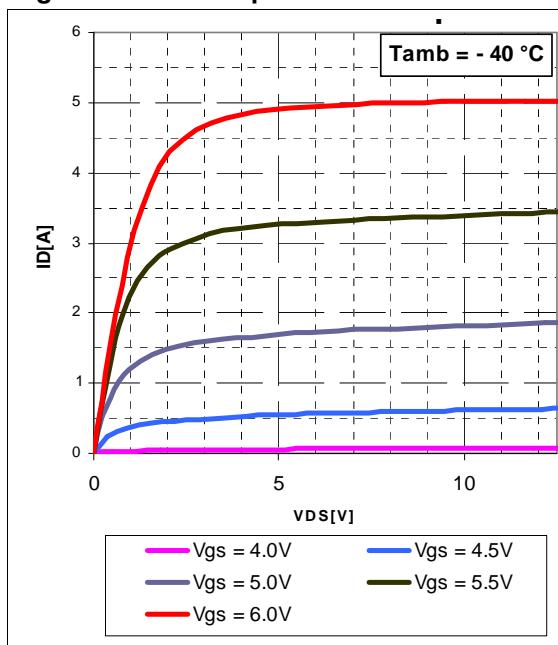
Freq. (MHz)	$Z_{IN} (\Omega)$	$Z_{DL} (\Omega)$
870 MHz	TBD	TBD

## 4 Typical performance

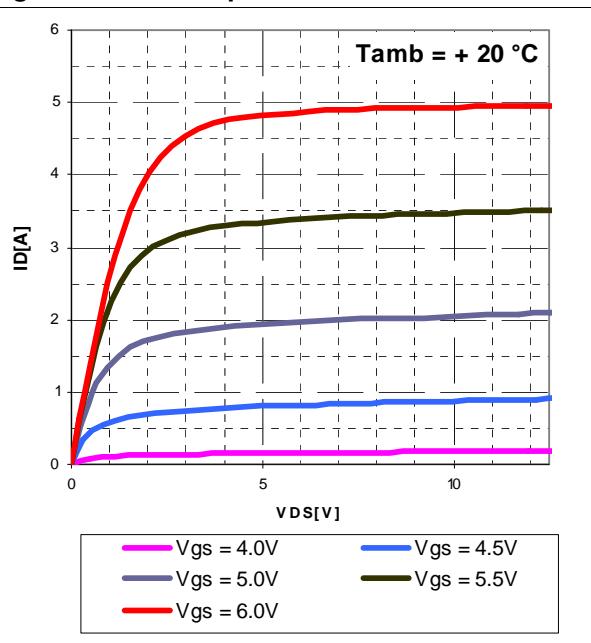
**Figure 3. Capacitances vs drain voltage**

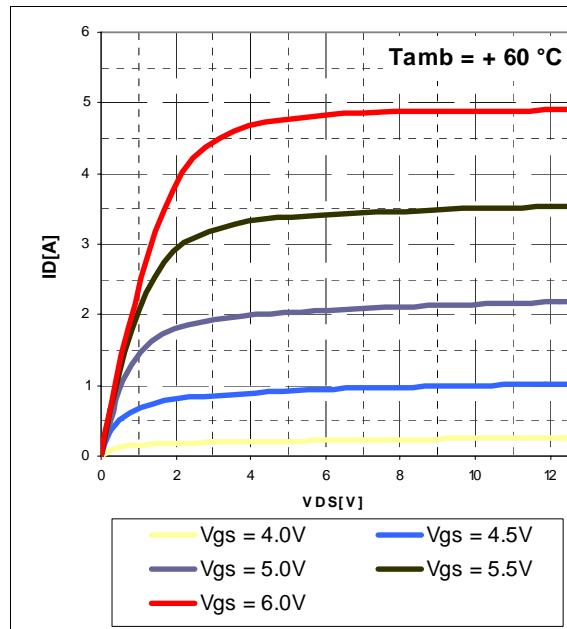
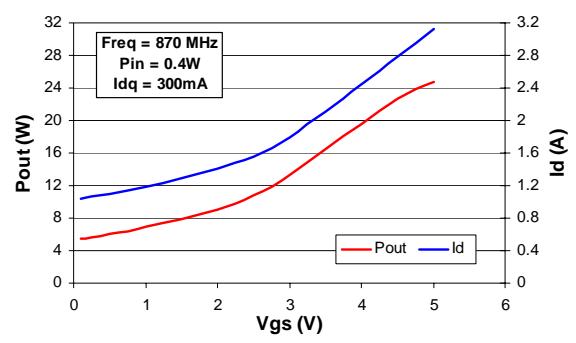
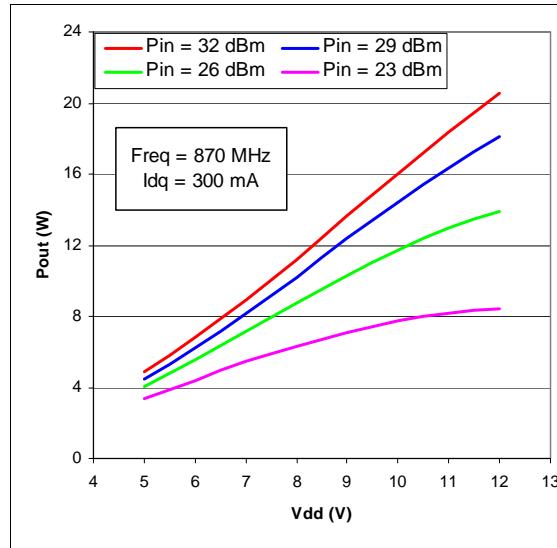
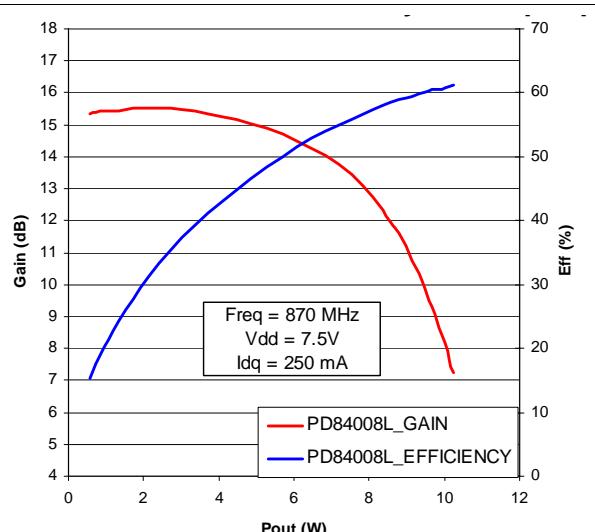


**Figure 4. DC output characteristics**

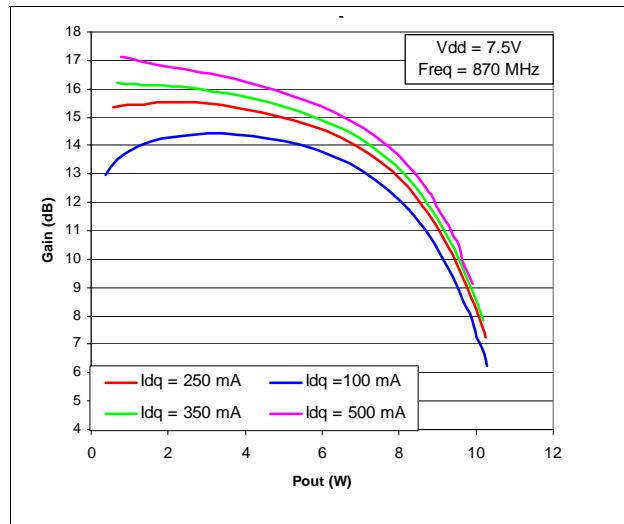


**Figure 5. DC output characteristics**



**Figure 6. DC output characteristics****Figure 7. Output power and drain current vs gate voltage****Figure 8. Output power vs supply voltage and input power****Figure 9. Gain and efficiency vs output power**

**Figure 10. Gain vs output power and bias current**

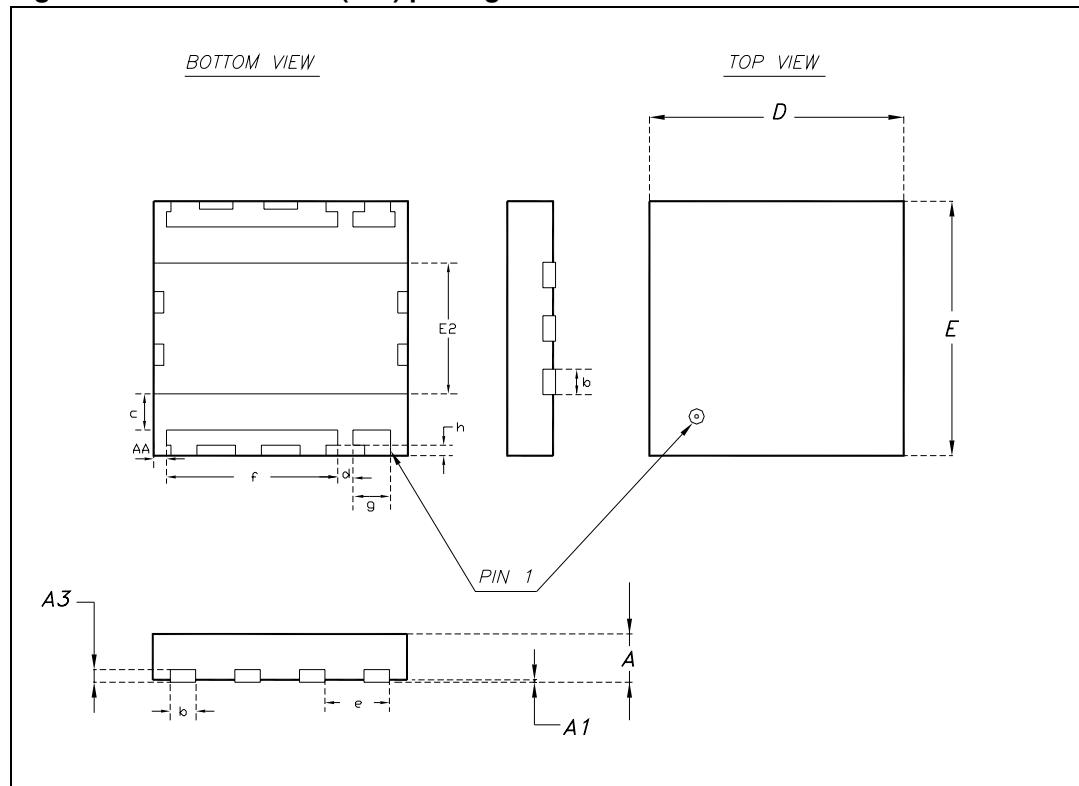


## 5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

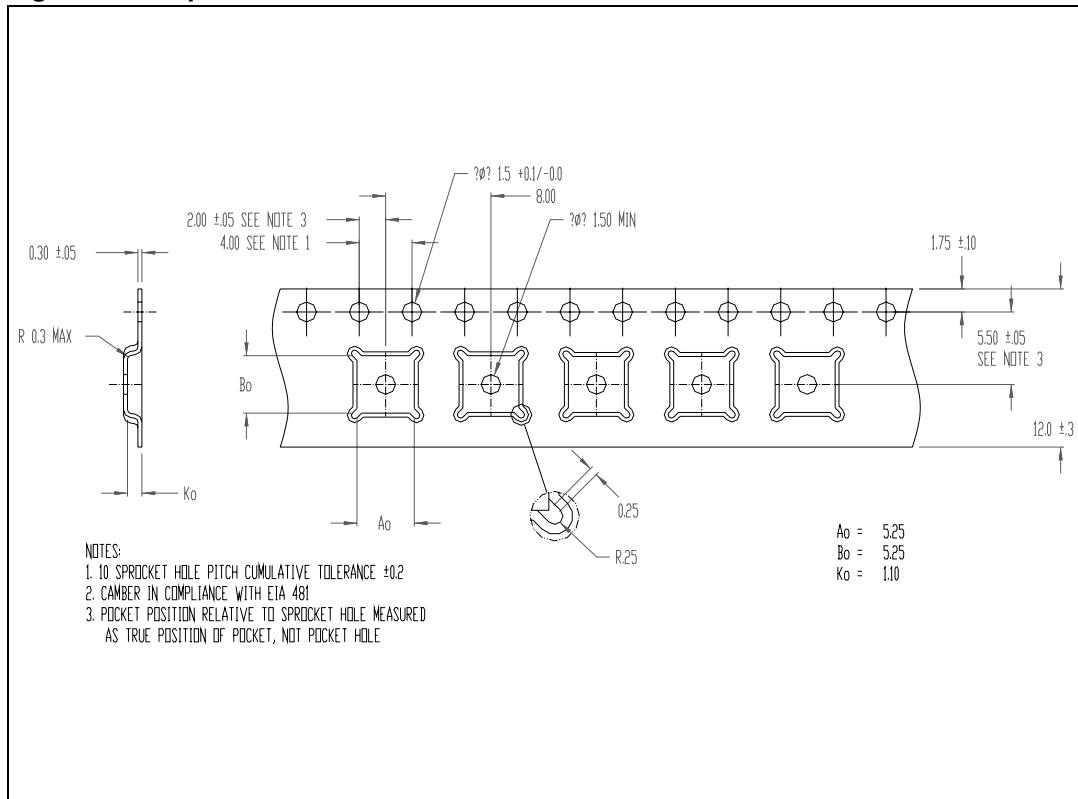
**Table 9. PowerFLAT™ (5x5) mechanical data**

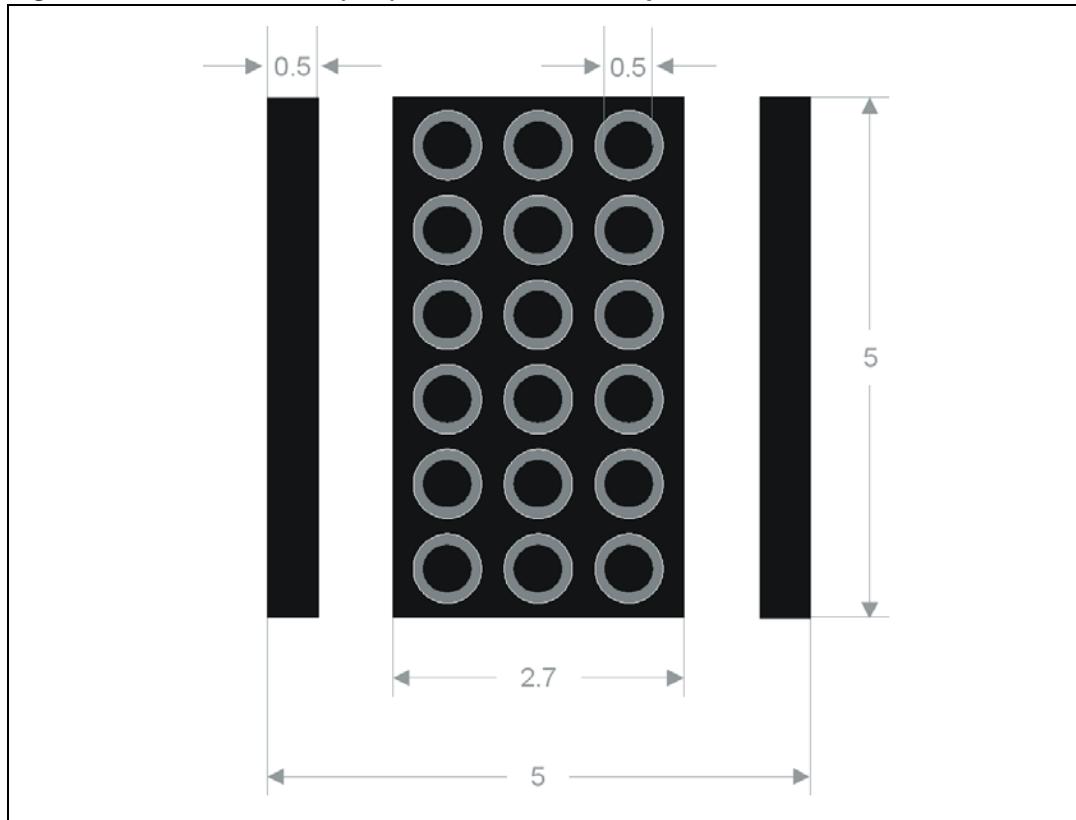
Dim.	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A		0.90	1.00		0.035	0.039
A1		0.02	0.05		0.001	0.002
A3		0.24			0.009	
AA	0.15	0.25	0.35	0.006	0.01	0.014
b	0.43	0.51	0.58	0.017	0.020	0.023
c	0.64	0.71	0.79	0.025	0.028	0.031
D		5.00			0.197	
d		0.30			0.011	
E		5.00			0.197	
E2	2.49	2.57	2.64	0.098	0.101	0.104
e		1.27			0.050	
f		3.37			0.132	
g		0.74			0.03	
h		0.21			0.008	

**Figure 11. PowerFLAT™ (5x5) package dimensions**

**Table 10. Tape and reel dimensions**

Dim.	Mm		
	Min	Typ	Max
Ao	5.15	5.25	5.35
Bo	5.15	5.25	5.35
Ko	1.0	1.1	1.2

**Figure 12. Tape and reel dimensions**

**Figure 13. PowerFLAT™ (5x5) recommended footprint**

## 6 Revision history

**Table 11. Document revision history**

Date	Revision	Changes
05-Dec-2007	1	Initial release.
05-Mar-2008	2	Updated <a href="#">Table 4 on page 4</a> .
15-Feb-2011	3	Updated <a href="#">Table 4 on page 4</a>

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